

# RENESAS Low Skew, 1-to-4 LVCMOS/LVTTL-to-LVDS Fanout Buffer

### DATASHEET

### **General Description**

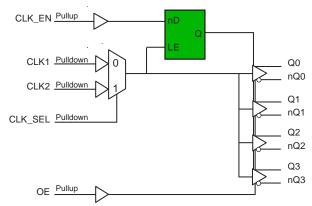
The 8545I-02 is a low skew, high performance 1-to-4 LVCMOS/LVTTL-to-LVDS Clock Fanout Buffer. Utilizing Low Voltage Differential Signaling (LVDS) the 8545I-02 provides a low power, low noise, solution for distributing clock signals over controlled impedances of 100 $\Omega$ . The 8545I-02 accepts an LVCMOS/LVTTL input level and translates it to 3.3V LVDS output levels.

Guaranteed output and part-to-part skew characteristics make the 8545I-02 ideal for those applications demanding well defined performance and repeatability.

### Features

- Four differential LVDS output pairs
- Two LVCMOS/LVTTL clock inputs to support redundant or selectable frequency fanout applications
- Maximum output frequency: 350MHz
- Translates LVCMOS/LVTTL input signals to LVDS levels
- Output skew: 60ps (maximum)
- Part-to-part skew: 450ps (maximum)
- Propagation delay: 1.45ns (maximum)
- Additive phase jitter, RMS: 0.14ps (typical)
- Full 3.3V supply mode
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

# **Block Diagram**



# **Pin Assignment**

GND CLK_EN CLK_SEL CLK1 nc CLK2	1 2 3 4 5 6	20 19 18 17 16 15	Q0 nQ0 VDD Q1 nQ1 Q2
CLK1	4	17	□Q1
nc	5	16	🗆 nQ1
CLK2	6	15	🗆 Q2
nc	7	14	🗆 nQ2
OE	8	13	GND
GND 🗌	9	12	🗆 Q3
V <sub>DD</sub> 🗆	10	11	🗆 nQ3

8545I-02

20-Lead TSSOP 6.5mm x 4.4mm x 0.925mm package body G Package Top View

Number	Name	Ţ	уре	Description
1, 9, 13	GND	Power		Power supply ground.
2	CLK_EN	Input	Pullup	Synchronizing clock enable. When HIGH, clock outputs follows clock input. When LOW, Qx outputs are forced low, nQx outputs are forced high. LVCMOS / LVTTL interface levels.
3	CLK_SEL	Input	Pulldown	Clock select input. When HIGH, selects CLK2 input. When LOW, selects CLK1 input. LVCMOS / LVTTL interface levels.
4	CLK1	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTL interface levels.
5, 7	nc	Unused		No connect.
6	CLK2	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTL interface levels.
8	OE	Input	Pullup	Output enable. Controls enabling and disabling of outputs Q0/nQ0 through Q3/nQ3. LVCMOS/LVTTL interface levels.
10, 18	V <sub>DD</sub>	Power		Positive supply pins.
11, 12	nQ3, Q3	Output		Differential output pair. LVDS interface levels.
14, 15	nQ2, Q2	Output		Differential output pair. LVDS interface levels.
16, 17	nQ1, Q1	Output		Differential output pair. LVDS interface levels.
19, 20	nQ0, Q0	Output		Differential output pair. LVDS interface levels.

# Table 1. Pin Descriptions

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

# **Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		рF
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ

# **Function Tables**

### Table 3A. Control Input Function Table

	Inputs				puts
OE	CLK_EN	CLK_SEL	Selected Source	Q0:Q3	nQ0:nQ3
0	X	Х		High-Impedance	High-Impedance
1	0	0	CLK1	Low	High
1	0	1	CLK2	Low	High
1	1	0	CLK1	Active	Active
1	1	1	CLK2	Active	Active

After CLK\_EN switches, the clock outputs are disabled or enabled following a rising and falling input clock edge as shown in Figure 1. In the active mode, the state of the outputs are a function of the CLK1 and CLK2 inputs as described in Table 3B.

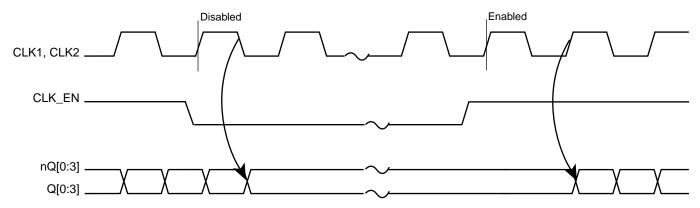


Figure 1. CLK\_EN Timing Diagram

### Table 3B. Clock Input Function Table

Inputs	Outputs		
CLK1 or CLK2	Q0:Q3	nQ0:nQ3	
0	LOW	HIGH	
1	HIGH	LOW	

# **Absolute Maximum Ratings**

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V <sub>DD</sub>	4.6V
Inputs, V <sub>I</sub>	-0.5V to V <sub>DD</sub> + 0.5V
Outputs, I <sub>O</sub> Continuos Current Surge Current	10mA 15mA
Package Thermal Impedance, $\theta_{JA}$	91.1°C/W (0 mps)
Storage Temperature, T <sub>STG</sub>	-65°C to 150°C

# **DC Electrical Characteristics**

### Table 4A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>DD</sub>	Positive Supply Voltage		3.135	3.3	3.465	V
I <sub>DD</sub>	Power Supply Current				90	mA

### Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V <sub>IH</sub>	Input High Voltage			2		V <sub>DD</sub> + 0.3	V
V <sub>IL</sub>	Input Low Volt	age		-0.3		0.8	V
Input I <sub>IH</sub> High Current	Input	CLK1, CLK2, CLK_SEL	V <sub>DD</sub> = V <sub>IN</sub> = 3.465V			150	μA
	OE, CLK_EN	V <sub>DD</sub> = V <sub>IN</sub> = 3.465V			5	μA	
	Input	CLK1, CLK2, CLK_SEL	V <sub>DD</sub> = 3.465V, V <sub>IN</sub> = 0V	-5			μA
Low Cu	Low Current	OE, CLK_EN	V <sub>DD</sub> = 3.465V, V <sub>IN</sub> = 0V	-150			μA

### Table 4C. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ , $T_A = -40$ °C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>OD</sub>	Differential Output Voltage		275		525	mV
$\Delta V_{OD}$	V <sub>OD</sub> Magnitude Change				50	mV
V <sub>OS</sub>	Offset Voltage		1.1	1.25	1.4	V
$\Delta V_{OS}$	V <sub>OS</sub> Magnitude Change			5	50	mV

# **AC Electrical Characteristics**

Table 5. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f <sub>MAX</sub>	Output Frequency				350	MHz
t <sub>PD</sub>	Propagation Delay; NOTE 1		1.0		1.45	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section	155.52MHz, Integration Range: 12kHz – 20MHz		0.14		ps
<i>t</i> sk(o)	Output Skew; NOTE 2, 4				60	ps
<i>t</i> sk(pp)	Part-to-Part Skew; NOTE 3, 4				450	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	150		700	ps
odc		$f \leq 166 MHz$	45		55	%
	Output Duty Cycle; NOTE 5	<i>f</i> > 166MHz	40		60	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

All parameters measured at  $f_{MAX}$  unless noted otherwise.

NOTE 1: Measured from  $V_{DD}/2$  of the input to the differential output crossing point.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

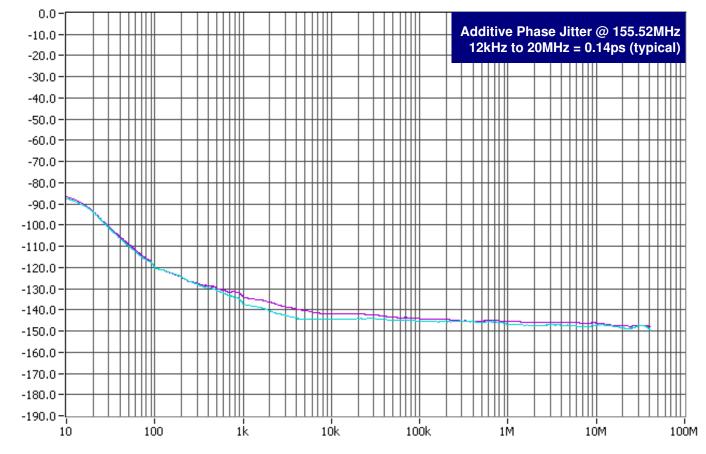
NOTE 5: Measured using 50% duty cycle.

SSB Phase Noise dBc/Hz

# **Additive Phase Jitter**

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise.* This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

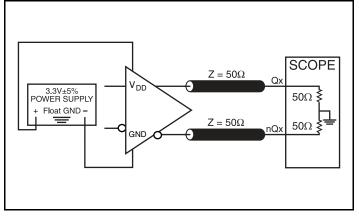
of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a *dBc* value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



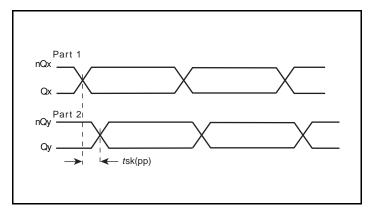
Offset from Carrier Frequency (Hz)

As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

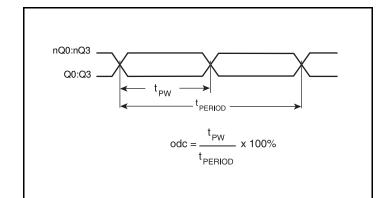
# **Parameter Measurement Information**



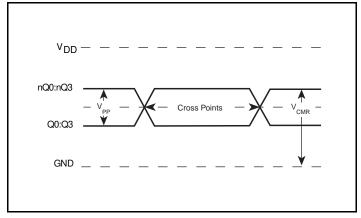
3.3V LVDS Output Load AC Test Circuit



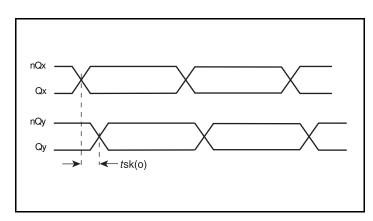
Part-to-Part Skew



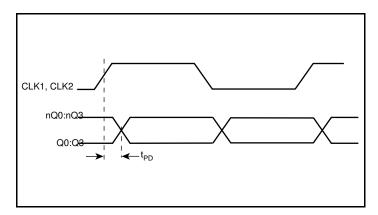
Output Duty Cycle/Pulse Width/Period



**Differential Output Level** 



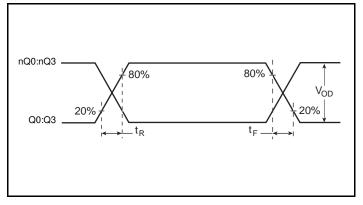
**Output Skew** 

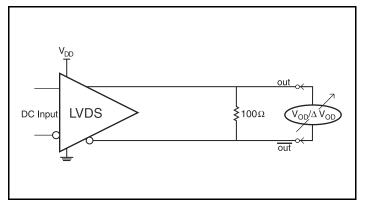




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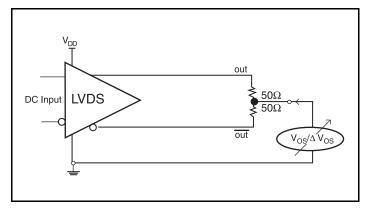
# Parameter Measurement Information, continued





**Differential Output Voltage Setup** 

### **Output Rise/Fall Time**



Offset Voltage Setup

# **Application Information**

### **Recommendations for Unused Input and Output Pins**

### Inputs:

### **CLK Inputs**

For applications not requiring the use of a clock input, it can be left floating. Though not required, but for additional protection, a  $1k\Omega$  resistor can be tied from the CLK input to ground.

### **LVCMOS Control Pins**

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A  $1k\Omega$  resistor can be used.

### Outputs:

### LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with  $100\Omega$  across. If they are left floating, there should be no trace attached.

### 3.3V LVDS Driver Termination

A general LVDS interface is shown in Figure 2. In a  $100\Omega$  differential transmission line environment, LVDS drivers require a matched load termination of  $100\Omega$  across near the receiver input. For a multiple

LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.

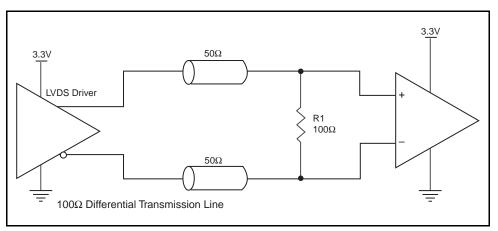


Figure 2. Typical LVDS Driver Termination

### **Power Considerations**

This section provides information on power dissipation and junction temperature for the 8545I-02. Equations and example calculations are also provided.

#### 1. Power Dissipation.

The total power dissipation for the 8545I-02 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

Power (core)<sub>MAX</sub> = V<sub>DD MAX</sub> \* I<sub>DD MAX</sub> = 3.465V \* 90mA = **311.85mW** 

#### 2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS devices is 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

Tj = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

T<sub>A</sub> = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 91.1°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 85°C with all outputs switching is:

 $85^{\circ}C + 0.312W * 91.1^{\circ}C/W = 113.4^{\circ}C$ . This is well below the limit of  $125^{\circ}C$ .

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

#### Table 6. Thermal Resistance $\theta_{JA}$ for 20 Lead TSSOP, Forced Convection

$\theta_{JA}$ by Velocity				
Meters per Second	0	1	2.5	
Multi-Layer PCB, JEDEC Standard Test Boards	91.1°C/W	86.7°C/W	84.6°C/W	



### **Reliability Information**

Table 7.  $\theta_{\text{JA}}$  vs. Air Flow Table for a 20 Lead TSSOP

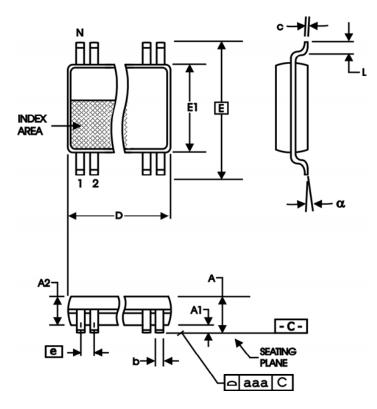
$\theta_{JA}$ by Velocity				
Meters per Second	0	1	2.5	
Multi-Layer PCB, JEDEC Standard Test Boards	91.1°C/W	86.7°C/W	84.6°C/W	

### **Transistor Count**

The transistor count for 8545I-02 is: 360

# Package Outline and Package Dimensions

Package Outline - G Suffix for 20 Lead TSSOP



#### **Table 8. Package Dimensions**

Table 6. Package Dimensions					
All Dimensions in Millimeters					
Symbol	Minimum Maximum				
N	20				
A		1.20			
A1	0.05	0.15			
A2	0.80	1.05			
b	0.19	0.30			
C	0.09	0.20			
D	6.40	6.60			
E	6.40 Basic				
E1	4.30	4.50			
е	0.65 Basic				
L	0.45	0.75			
α	0°	8°			
aaa		0.10			

Reference Document: JEDEC Publication 95, MO-153



# **Ordering Information**

### Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8545AGI-02LF	ICS8545AI02L	"Lead-Free" 20 Lead TSSOP	Tube	-40°C to 85°C
8545AGI-02LFT	ICS8545AI02L	"Lead-Free" 20 Lead TSSOP	2500 Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

Revision History5/7/15Product Discontinuation Notice - PDN CQ-15-03.



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